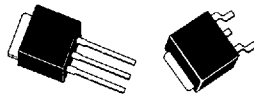


# 2SJ191



2083A

2092A

LD (Low Drive) Series  $V_{DSS}=60V$

## P Channel Power MOSFET

©3764A

### Features

- Low ON resistance
- Very high-speed switching
- Low-voltage drive

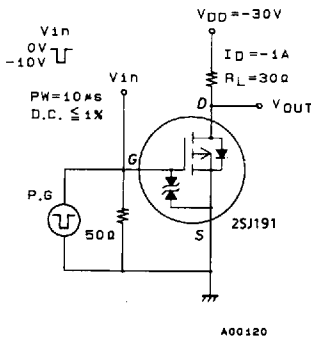
### Absolute Maximum Ratings at $T_a=25^\circ C$

			unit
Drain to Source Voltage	$V_{DSS}$	-60	V
Gate to Source Voltage	$V_{GSS}$	$\pm 15$	V
Drain Current (DC)	$I_D$	-2	A
Drain Current (Pulse)	$I_{DP}$	$PW \leq 10\mu s, \text{ duty cycle} \leq 1\%$	A
Allowable Power Dissipation	$P_D$	$T_c=25^\circ C$	20
Channel Temperature	$T_{ch}$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ C$

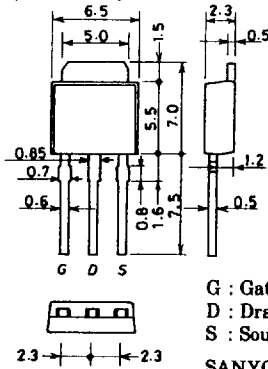
### Electrical Characteristics at $T_a=25^\circ C$

			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1mA, V_{GS} = 0$	-60			V
G-S Breakdown Voltage	$V_{(BR)GSS}$	$I_G = \pm 100\mu A, V_{DS} = 0$	$\pm 15$			V
Zero Gate Voltage	$I_{DSS}$	$V_{DS} = -60V, V_{GS} = 0$			-100	$\mu A$
Drain Current						
Gate to Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 12V, V_{DS} = 0$			$\pm 10$	$\mu A$
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10V, I_D = -1mA$	-1.0		-2.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10V, I_D = -1A$	1.2	2		S
Static Drain to Source on State Resistance	$R_{DS(on)}$	$I_D = -1A, V_{GS} = -10V$		0.35	0.45	$\Omega$
	$R_{DS(on)}$	$I_D = -1A, V_{GS} = -4V$		0.45	0.6	$\Omega$
Input Capacitance	$C_{iss}$	$V_{DS} = -20V, f = 1MHz$		380		pF
Output Capacitance	$C_{oss}$	$V_{DS} = -20V, f = 1MHz$		150		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS} = -20V, f = 1MHz$		40		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit		12		ns
Rise Time	$t_r$	"		18		ns
Turn-OFF Delay Time	$t_{d(off)}$	"		85		ns
Fall Time	$t_f$	"		55		ns
Diode Forward Voltage	$V_{SD}$	$I_S = -2A, V_{GS} = 0$	-1.0	-1.5		V

### Switching Time Test Circuit

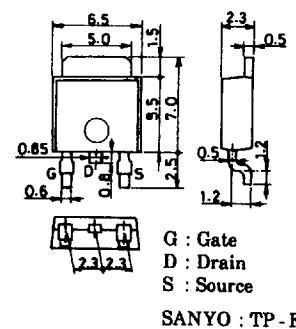


### Package Dimensions 2083A (unit: mm)



G : Gate  
D : Drain  
S : Source  
SANYO : TP

### Package Dimensions 2092A (unit: mm)



G : Gate  
D : Drain  
S : Source  
SANYO : TP-FA

